

## LOW DROP POWER SCHOTTKY RECTIFIER

### MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 8 A
$V_{RRM}$	45 V
$T_j$ (max)	150 °C
$V_F$ (max)	0.45 V

### FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW SWITCHING LOSSES ALLOWING HIGH FREQUENCY OPERATION
- INSULATED PACKAGE: TO-220FPAB  
Insulated voltage: 2000V DC  
Capacitance: 12 pF
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

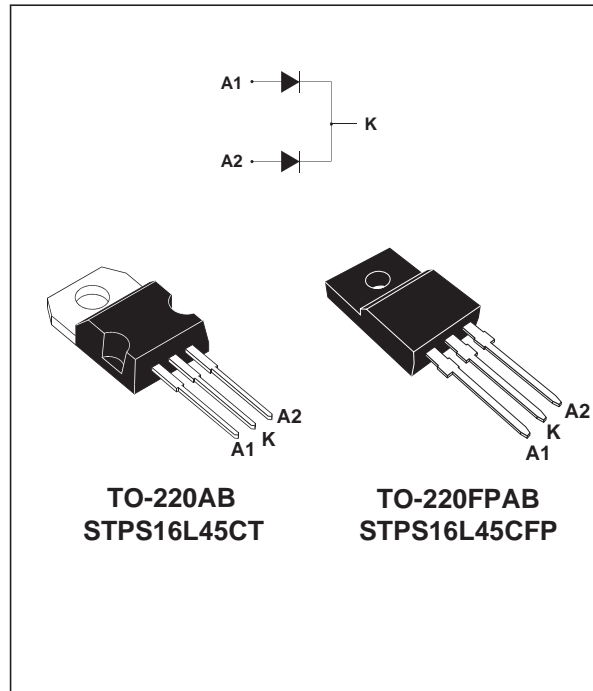
Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AB and TO-220FPAB, these devices are intended for use in low voltage, high frequency converters, free-wheeling and polarity protection applications.

### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage			45	V	
$I_{F(RMS)}$	RMS forward current			30	A	
$I_{F(AV)}$	Average forward current	TO-220AB	$T_c = 140^\circ\text{C}$ $\delta = 0.5$	Per diode	8	A
				Per device	16	
		TO-220FPAB	$T_c = 125^\circ\text{C}$ $\delta = 0.5$	Per diode	8	A
				Per device	16	
$I_{FSM}$	Surge non repetitive forward current		$t_p = 10$ ms sinusoidal	180	A	
$I_{RRM}$	Repetitive peak reverse current		$t_p = 2$ $\mu\text{s}$ square F=1kHz	1	A	
$I_{RSM}$	Non repetitive peak reverse current		$t_p = 100$ $\mu\text{s}$ square	2	A	
$P_{ARM}$	Repetitive peak avalanche power		$t_p = 1$ $\mu\text{s}$ $T_j = 25^\circ\text{C}$	4000	W	
$T_{stg}$	Storage temperature range			- 65 to + 150	°C	
$T_j$	Maximum operating junction temperature *			150	°C	
dV/dt	Critical rate of rise of reverse voltage			10000	V/ $\mu\text{s}$	

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$  thermal runaway condition for a diode on its own heatsink



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## THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	TO-220AB	Per diode	2.2
			Total	1.3
			Coupling	0.3
		TO-220FPAB	Per diode	4.5
			Total	3.5
			Coupling	2.5

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

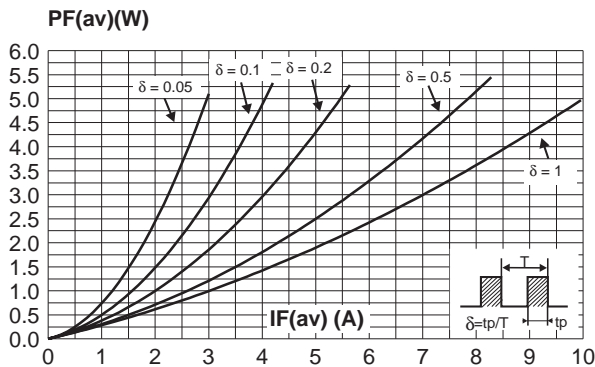
## STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			0.2	mA
		$T_j = 125^\circ\text{C}$			65	130	mA
$V_F^*$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 8\text{ A}$			0.5	V
		$T_j = 125^\circ\text{C}$			0.39	0.45	
		$T_j = 25^\circ\text{C}$	$I_F = 16\text{ A}$			0.63	
		$T_j = 125^\circ\text{C}$			0.55	0.64	

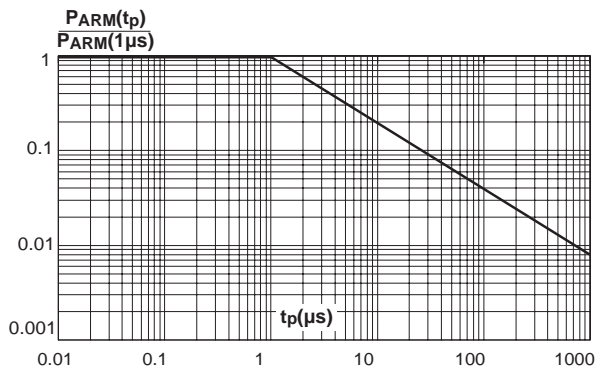
Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation :  
 $P = 0.26 \times I_{F(AV)} + 0.024 I_{F(RMS)}^2$

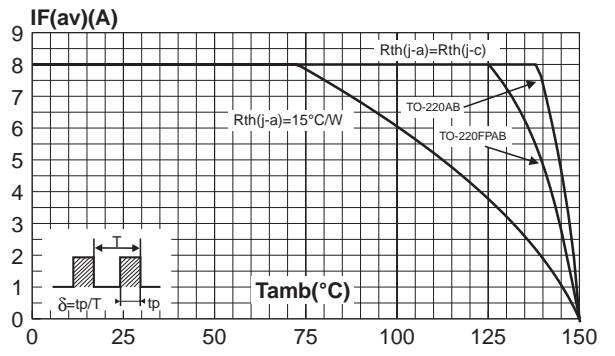
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



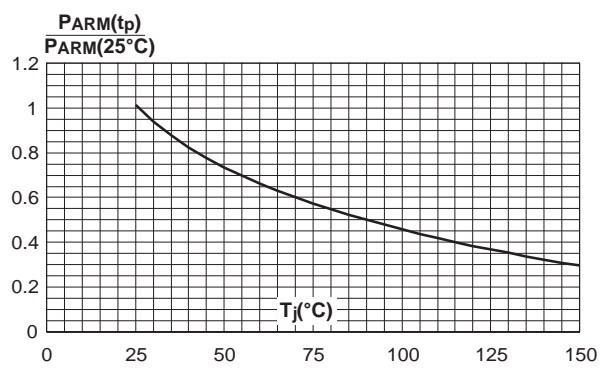
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



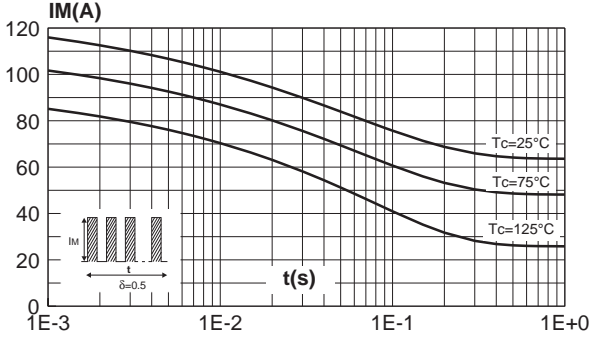
**Fig. 2:** Average current versus ambient temperature ( $\delta = 0.5$ ) (per diode).



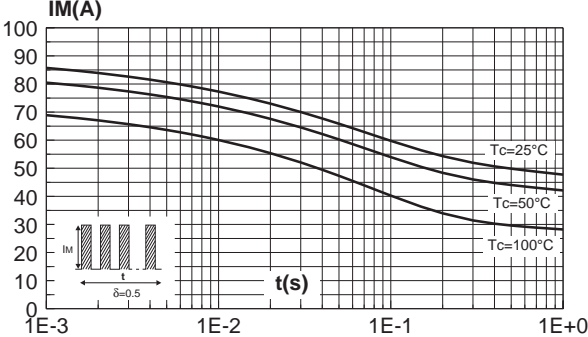
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



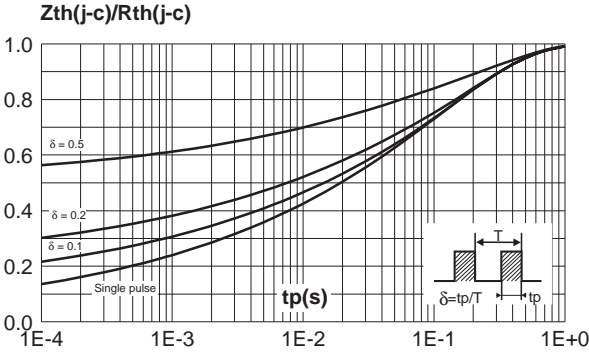
**Fig. 5-1:** Non repetitive surge peak forward current versus overload duration (maximum values per diode, TO-220AB).



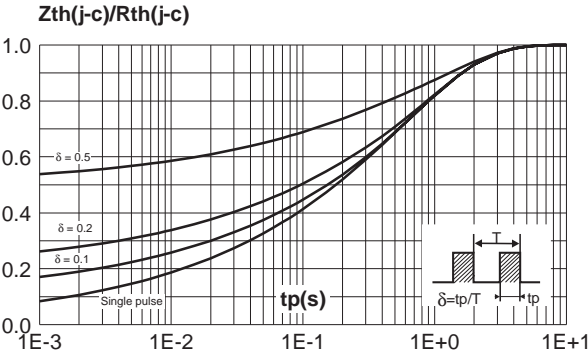
**Fig. 5-2:** Non repetitive surge peak forward current versus overload duration (maximum values per diode, TO-220FPAB).



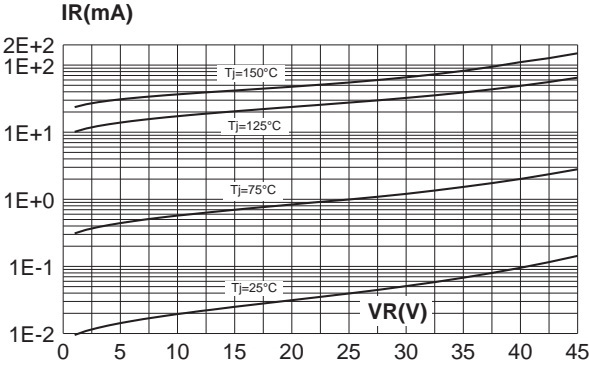
**Fig. 6-1:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220AB).



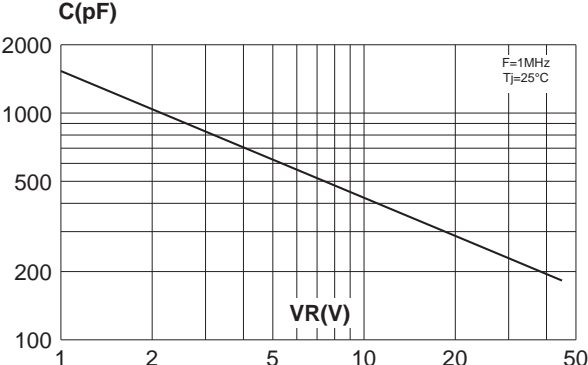
**Fig. 6-2:** Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB).



**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values) (per diode).

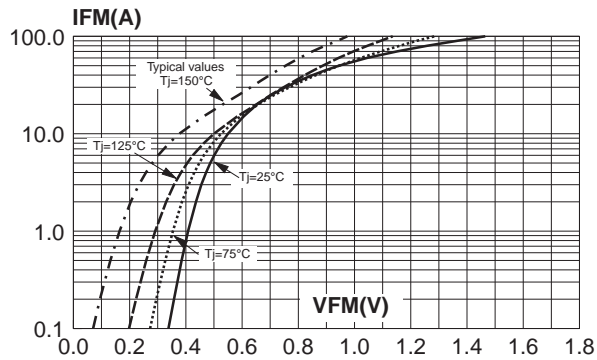


**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values) (per diode).



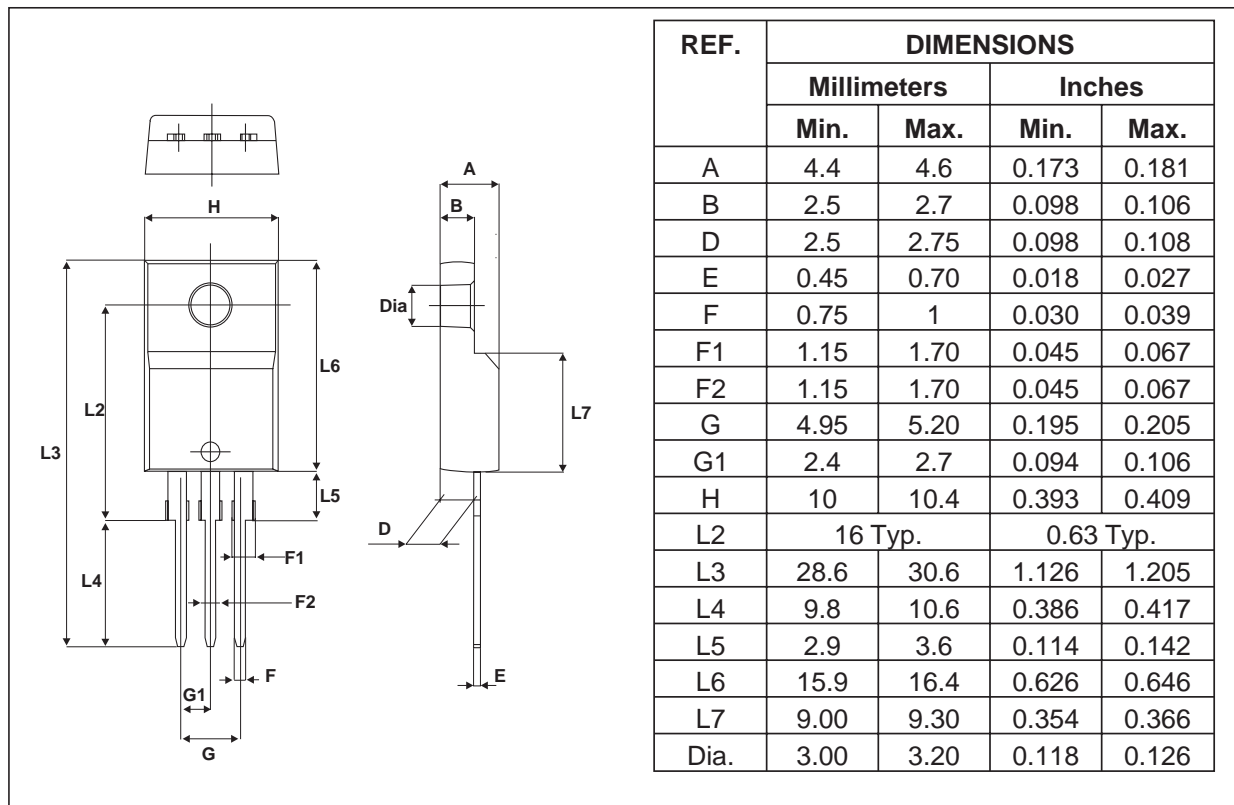
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**Fig. 9:** Forward voltage drop versus forward current (maximum values) (per diode).



## PACKAGE MECHANICAL DATA

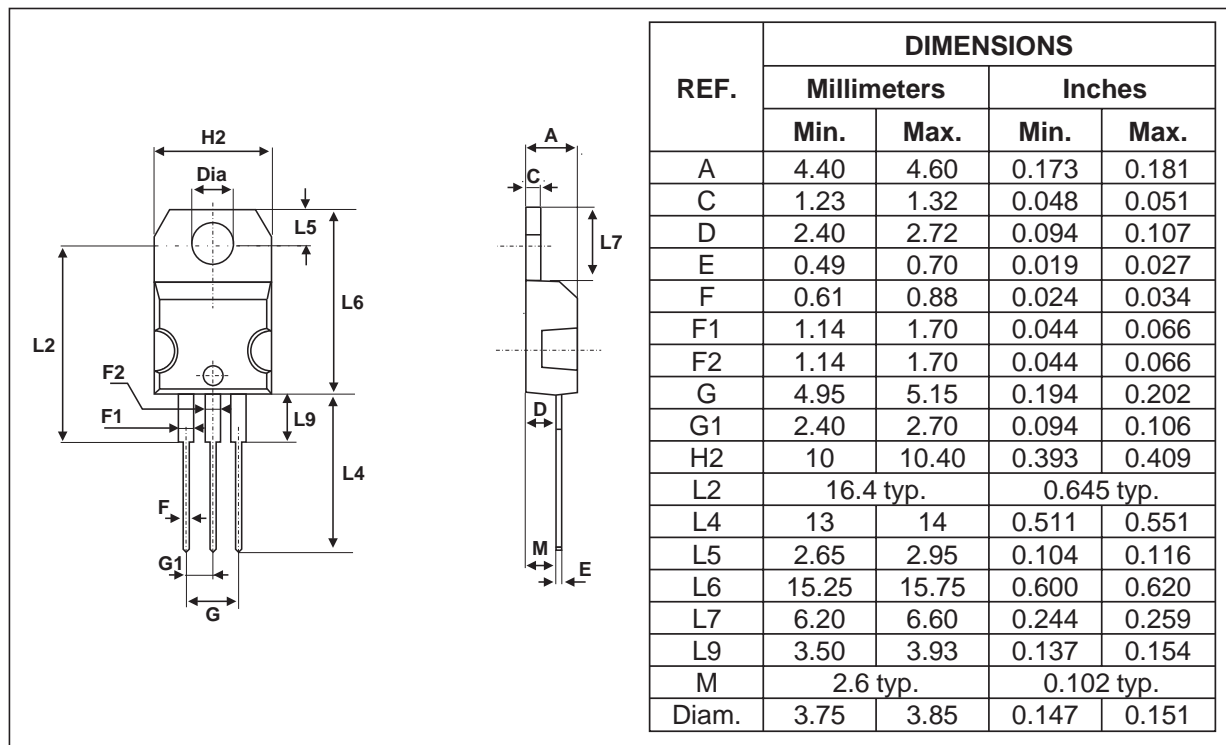
TO-220FPAB



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## PACKAGE MECHANICAL DATA

TO-220AB



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS16L45CT	STPS16L45CT	TO-220AB	2g	50	Tube
STPS16L45CFP	STPS16L45CFP	TO-220FPAB	2g	50	Tube

- Epoxy meets UL94,V0
- Cooling method : C
- Recommended torque value : 0.55 m.N
- Maximum torque value : 0.70 m.N

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